



直径 Diameter	150.0 mm ± 0.25 mm
表面取向 Surface orientation	4.0° toward <11-20> ± 0.5°
主参考面取向 Primary flat orientation	<11-20> ± 5°
副参考面取向 Secondary flat orientation	N/A
主参考面长度 Primary flat length	47.5± 2.5 mm
副参考面长度 Secondary flat length	None
晶片边缘 WaferEdge	Without Chamfer
微管密度 Micropipe densities	≤5 /cm ²
多型 (强光灯观测) Polytypeareas by high-intensity light	None permitted
电阻率 Resistivity	0.015~0.028 Ω·cm
厚度 Thickness	350 μm ± 50 μm
总厚度变化 TTV	≤10μm
弯曲度 (绝对值) Bow	≤40μm
翘曲度 Warp	≤60μm
表面处理 Surface finish	Double Side Polish, Si Face CMP (chemical polishing)
裂纹 (强光灯观测) Crack by high-intensity light	None permitted
崩边/缺口 (漫反射光观测) Edge chips/indents by diffuse lighting	None permitted